

FDMC8882

May 2014

N-Channel Power Trench® MOSFET **30 V, 16 A, 14.3 m** Ω

Features

- Max $r_{DS(on)}$ = 14.3 m Ω at V_{GS} = 10 V, I_D = 10.5 A
- Max $r_{DS(on)}$ = 22.5 m Ω at V_{GS} = 4.5 V, I_D = 8.3 A
- High performance technology for extremely low r_{DS(on)}
- Termination is Lead-free and RoHS Compliant

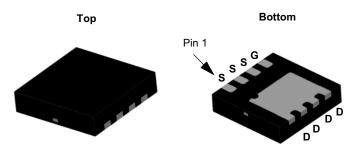


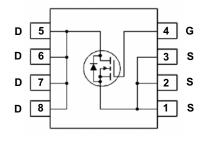
General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been especially tailored to minimize the on-state resistance. This device is well suited for Power Management and load switching applications common in Notebook Computers and Portable Battery Packs.

Application

- High side in DC DC Buck Converters
- Notebook battery power management
- Load switch in Notebook





MLP 3.3x3.3

MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter		Ratings	Units	
V_{DS}	Drain to Source Voltage			30	V
V_{GS}	Gate to Source Voltage			±20	V
I _D	Drain Current -Continuous (Package limited)	T _C = 25 °C		16	
	-Continuous (Silicon limited) T _C = 25 °C			34	
	-Continuous	T _A = 25 °C	(Note 1a)	10.5	A
	-Pulsed			40	
D	Power Dissipation	T _C = 25 °C		18	w
P_{D}	Power Dissipation	T _A = 25 °C	(Note 1a)	2.3	VV
T _J , T _{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	6.6	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC8882	FDMC8882	MLP 3.3x3.3	13 "	12 mm	3000 units

Electrical Characteristics T_J = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	octeristics					
BV _{DSS}	Drain to Source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0 V	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, referenced to 25 °C		25		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V			1	μА
I _{GSS}	Gate to Source Leakage Current	$T_J = 125 ^{\circ}\text{C}$ $V_{GS} = \pm 20 ^{\circ}\text{V}, V_{DS} = 0 ^{\circ}\text{V}$			250 ±100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	1.2	1.9	2.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I _D = 250 μA, referenced to 25 °C		-5		mV/°C
		V _{GS} = 10 V, I _D = 10.5 A		12.4	14.3	
r	Static Drain to Source On Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 8.3 \text{ A}$		16.0	22.5	mΩ
r _{DS(on)} Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 10.5 \text{ A}$ $T_J = 125 ^{\circ}\text{C}$		17.4		- 11152	
9 _{FS}	Forward Transconductance	V _{DD} = 5 V, I _D = 10.5 A		33		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V - 15 V V - 0 V	710	945	pF
C _{oss}	Output Capacitance	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	140	185	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 WI 12	90	135	pF
R_g	Gate Resistance		1.0		Ω

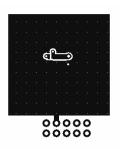
Switching Characteristics

t _{d(on)}	Turn-On Delay Time		7	14	ns
t _r	Rise Time	V _{DD} = 15 V, I _D = 10.5 A,	3	10	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_{GEN} = 6 Ω	17	30	ns
t _f	Fall Time		2	10	ns
0	Total Gate Charge	V _{GS} = 0 V to 10 V	14	20	nC
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0 \text{ V to } 4.5 \text{ V}$ $V_{DD} = 15 \text{ V}$	7	10	nC
Q_{gs}	Total Gate Charge	I _D = 10.5 A	2.3		nC
Q _{gd}	Gate to Drain "Miller" Charge		2.8		nC

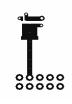
Drain-Source Diode Characteristics

TVob 1500fce to Drain Dione Forward Voltage	Source to Drain Diade, Forward Voltage	V _{GS} = 0 V, I _S = 10.5 A (Note 2)		0.88 1	1.2		
	$V_{GS} = 0 \text{ V}, I_S = 1.9 \text{ A}$ (Note 2)		0.76	1.2	v		
t _{rr}	Reverse Recovery Time	-I _F = 10.5 A, di/dt = 100 A/μs		16	28	ns	
Q _{rr}	Reverse Recovery Charge			4.4	10	nC	

^{1.} $R_{\theta JA}$ is determined with the device mounted on a 1 in 2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 53 °C/W when mounted on a 1 in² pad of 2 oz copper



b.125 °C/W when mounted on a minimum pad of 2 oz copper

^{2.} Pulse Test: Pulse Width < 300 $\mu s,$ Duty cycle < 2.0 %.

Typical Characteristics T_J = 25 °C unless otherwise noted

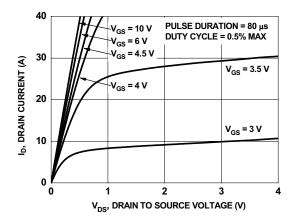


Figure 1. On-Region Characteristics

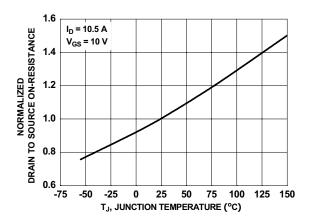


Figure 3. Normalized On-Resistance vs Junction Temperature

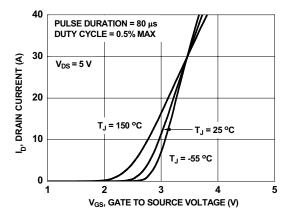


Figure 5. Transfer Characteristics

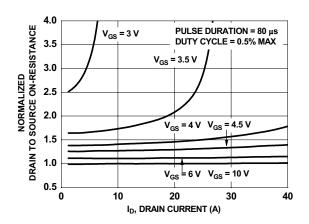


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

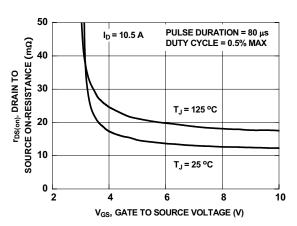


Figure 4. On-Resistance vs Gate to Source Voltage

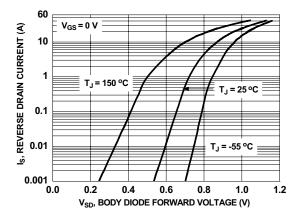


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25 °C unless otherwise noted

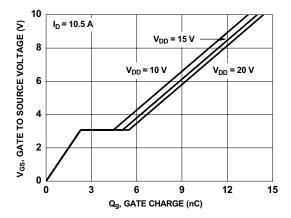


Figure 7. Gate Charge Characteristics

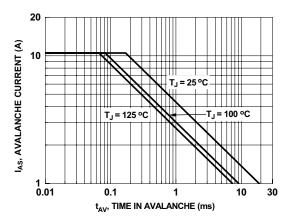


Figure 9. Unclamped Inductive Switching Capability

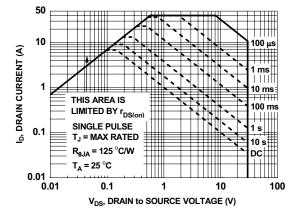


Figure 11. Forward Bias Safe Operating Area

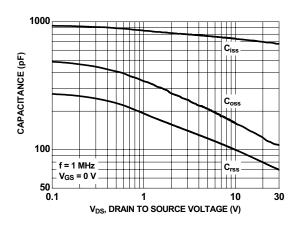


Figure 8. Capacitance vs Drain to Source Voltage

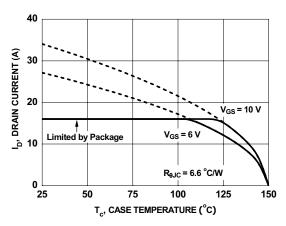


Figure 10. Maximum Continuous Drain Current vs Case Temperature

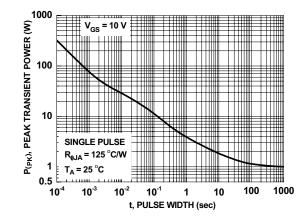


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted

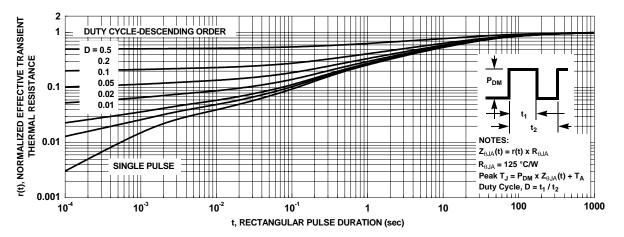
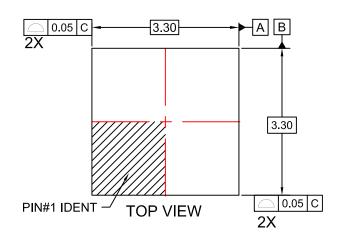
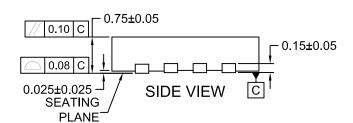
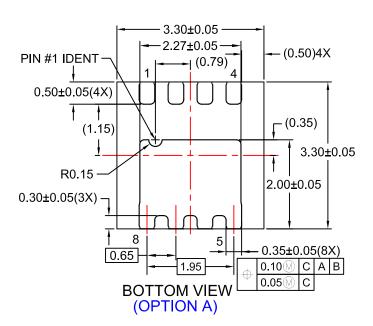
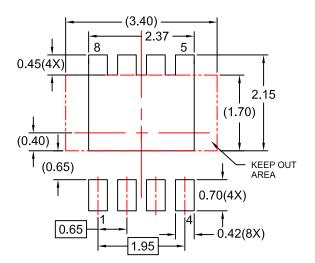


Figure 13. Transient Thermal Response Curve

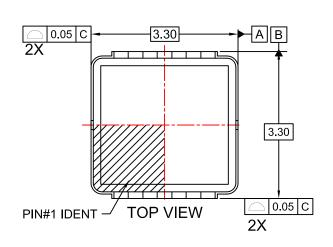


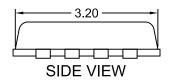


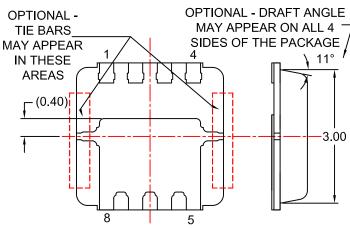




RECOMMENDED LAND PATTERN

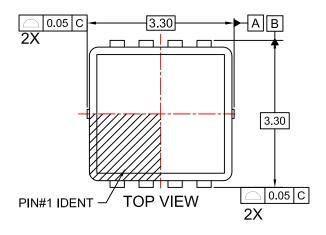


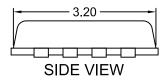


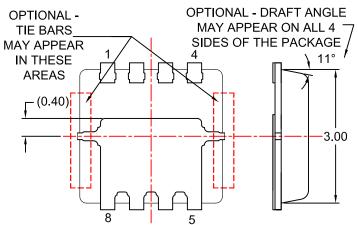


ALL DIMENSIONS AS PER OPTION A
UNLESS SPECIFIED
BOTTOM VIEW
(OPTION B)









ALL DIMENSIONS AS PER OPTION A
UNLESS SPECIFIED
BOTTOM VIEW
(OPTION C)

NOTES:

- A. PACKAGE DOES NOT FULLY CONFORM TO JEDEC REGISTRATION MO-240.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN
- E. DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. BURRS OR MOLD FLASH SHALL NOT EXCEED 0.10MM.
- F. DRAWING FILENAME: MKT-MLP08Wrev3.
- G. OPTION A SAWN MLP, OPTIONS B & C PUNCH MLP.







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Definition of Terms

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Datasheet Identification	Product Status	Definition			
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.			
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.			
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.			
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